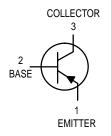
Amplifier Transistors PNP Silicon

2N4125 2N4126





MAXIMUM RATINGS

Rating	Symbol	2N4125	2N4126	Unit	
Collector-Emitter Voltage	VCEO	30	25	Vdc	
Collector-Base Voltage	VCBO	30	25	Vdc	
Emitter-Base Voltage	V _{EBO}	4.0		Vdc	
Collector Current — Continuous	IC	200		mAdc	
Total Device Dissipation @ T _A = 25°C Derate above 25°C	PD	625 5.0		mW mW/°C	
Total Device Dissipation @ T _C = 25°C Derate above 25°C	PD	1.5 12			
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150		°C	

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characterist	tic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I _C = 1.0 mAdc, I _B = 0)	2N4125 2N4126	V(BR)CEO	30 25	_ _	Vdc
Collector-Base Breakdown Voltage (I _C = 10 μAdc, I _E = 0)	2N4125 2N4126	V(BR)CBO	30 25	_	Vdc
Emitter-Base Breakdown Voltage (IE = 10 μAdc, IC = 0)		V(BR)EBO	4.0	_	Vdc
Collector Cutoff Current (V _{CB} = 20 Vdc, I _E = 0)		ICBO	_	50	nAdc
Emitter Cutoff Current (VEB = 3.0 Vdc, I _C = 0)		I _{EBO}	_	50	nAdc

^{1.} Pulse Test: Pulse Width \leq 300 $\mu s,$ Duty Cycle = 2.0%.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted) (Continued)

Characteristic		Symbol	Min	Max	Unit
ON CHARACTERISTICS				•	
DC Current Gain(1) (I _C = 2.0 mAdc, V _{CE} = 1.0 Vdc)	2N4125 2N4126	hFE	50 120	150 360	_
$(I_C = 50 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc})$	2N4125 2N4126		25 60	_	
Collector-Emitter Saturation Voltage ⁽¹⁾ (I _C = 50 mAdc, I _B = 5.0 mAdc)		VCE(sat)	_	0.4	Vdc
Base-Emitter Saturation Voltage(1) (IC = 50 mAdc, IB = 5.0 mAdc)		V _{BE} (sat)	_	0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS				•	
Current-Gain — Bandwidth Product (I _C = 10 mAdc, V _{CE} = 20 Vdc, f = 100 MHz)	2N4125 2N4126	fΤ	200 250	_	MHz
Input Capacitance (VEB = 0.5 Vdc, I _C = 0, f = 1.0 MHz)		C _{ibo}	_	10	pF
Collector–Base Capacitance (V _{CB} = 5.0 Vdc, I _E = 0, f = 1.0 MHz)		C _{cb}	_	4.5	pF
Small–Signal Current Gain (I _C = 2.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)	2N4125 2N4126	h _{fe}	50 120	200 480	_
Current Gain — High Frequency (IC = 10 mAdc, VCE = 20 Vdc, f = 100 MHz)	2N4125 2N4126	h _{fe}	2.0 2.5	_ 	_
Noise Figure (IC = 100 μ Adc, VCE = 5.0 Vdc, RS = 1.0 k ohm, f = 1.0 kHz)	2N4125 2N4126	NF		5.0 4.0	dB

^{1.} Pulse Test: Pulse Width $\leq 300~\mu s,$ Duty Cycle = 2.0%.

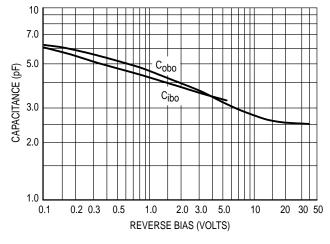


Figure 1. Capacitance

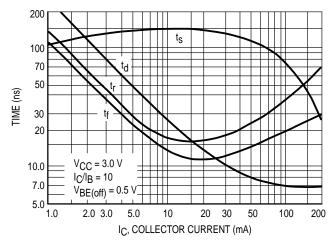
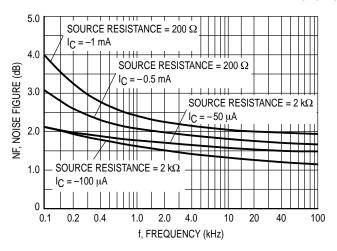


Figure 2. Switching Times

AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE

 $V_{CE} = -5.0 \text{ Vdc}, T_A = 25^{\circ}\text{C}$ Bandwidth = 1.0 Hz



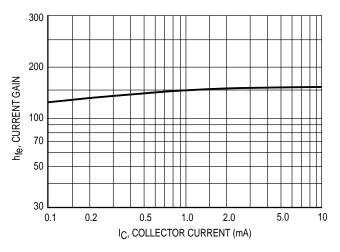
f = 1 kHz10 NF, NOISE FIGURE (dB) 8.0 6.0 4.0 $IC = 50 \mu A$ IC = 100 μA 2.0 0.2 20 0.1 0.4 10 40 100 RS, SOURCE RESISTANCE ($k\Omega$)

Figure 3. Frequency Variations

Figure 4. Source Resistance

h PARAMETERS

 $V_{CE} = 10 \text{ V}, f = 1 \text{ kHz}, T_A = 25^{\circ}\text{C}$



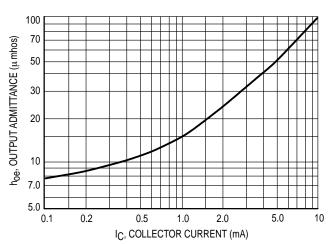
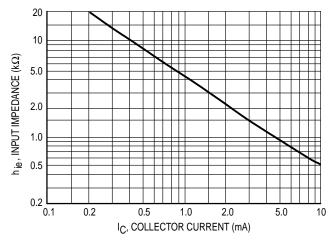


Figure 5. Current Gain

Figure 6. Output Admittance



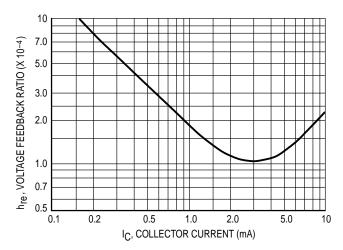


Figure 7. Input Impedance

Figure 8. Voltage Feedback Ratio

STATIC CHARACTERISTICS

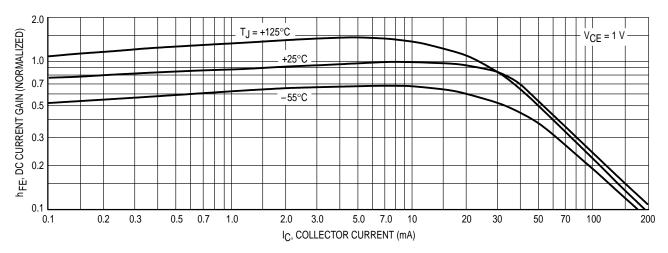


Figure 9. DC Current Gain

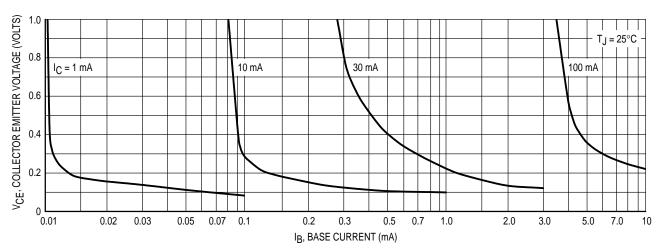


Figure 10. Collector Saturation Region

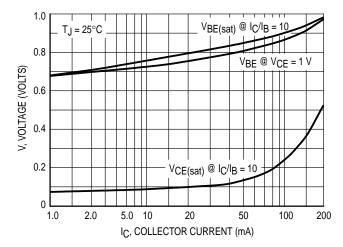


Figure 11. "On" Voltages

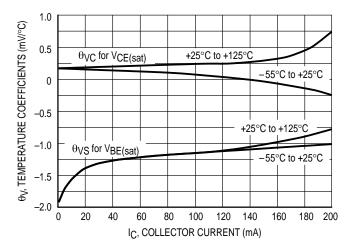
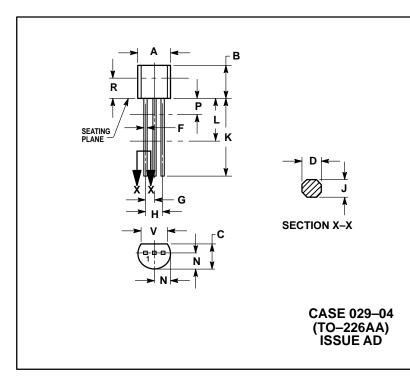


Figure 12. Temperature Coefficients

PACKAGE DIMENSIONS



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSION D AND J APPLY BETWEEN L AND K MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.022	0.41	0.55
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
ν	0.135		3 43	

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

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